

APPROVED O.G. FIG.
BY CLASS SUBCLASS
DRAFTSMAN

Title: Gallium Nitride Semiconductor . . . Source Device.
Inventor: Toshiyuki OKUMURA
Application No.: NEW
Docket No.: 204552016410

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Fig. 1

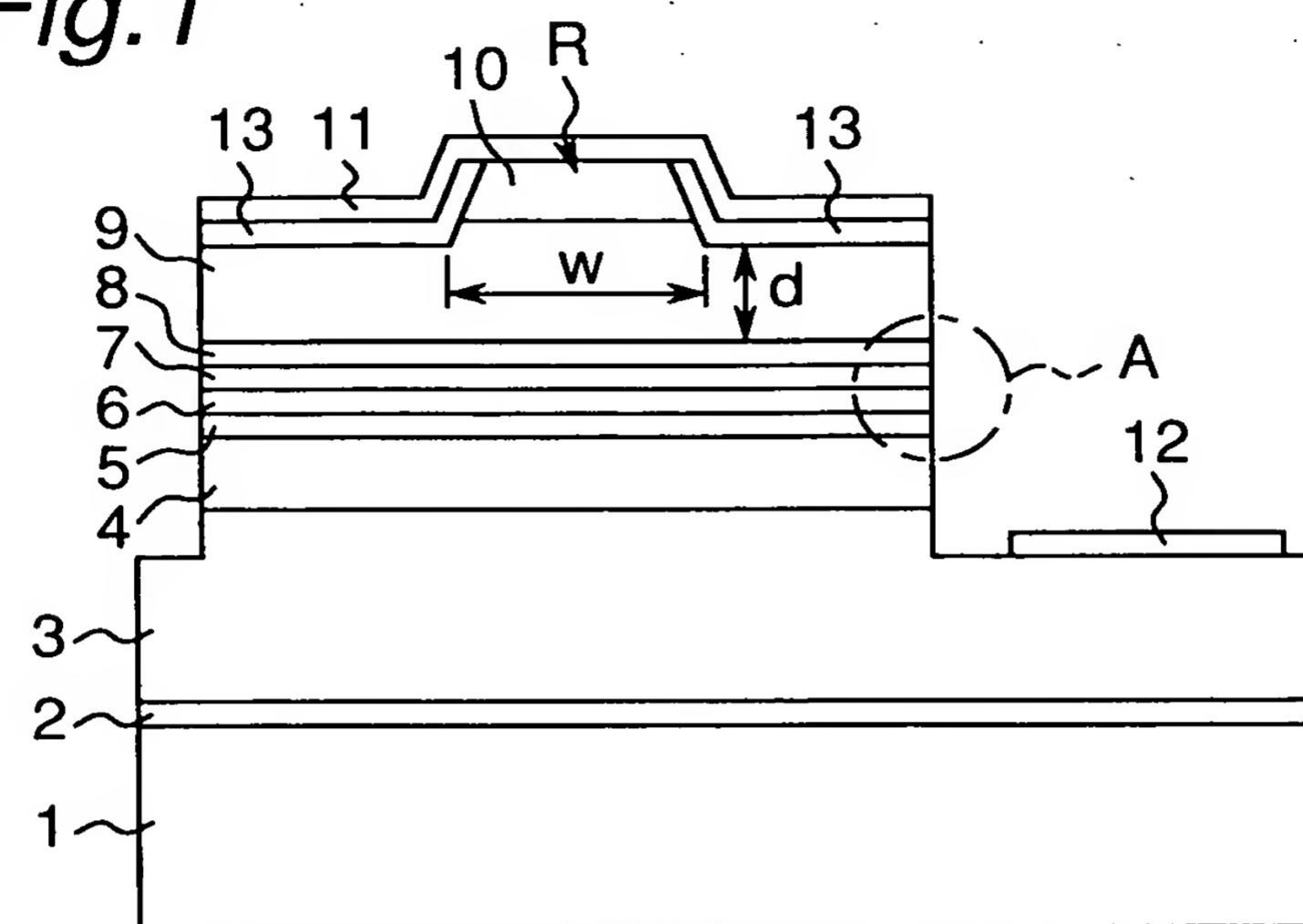
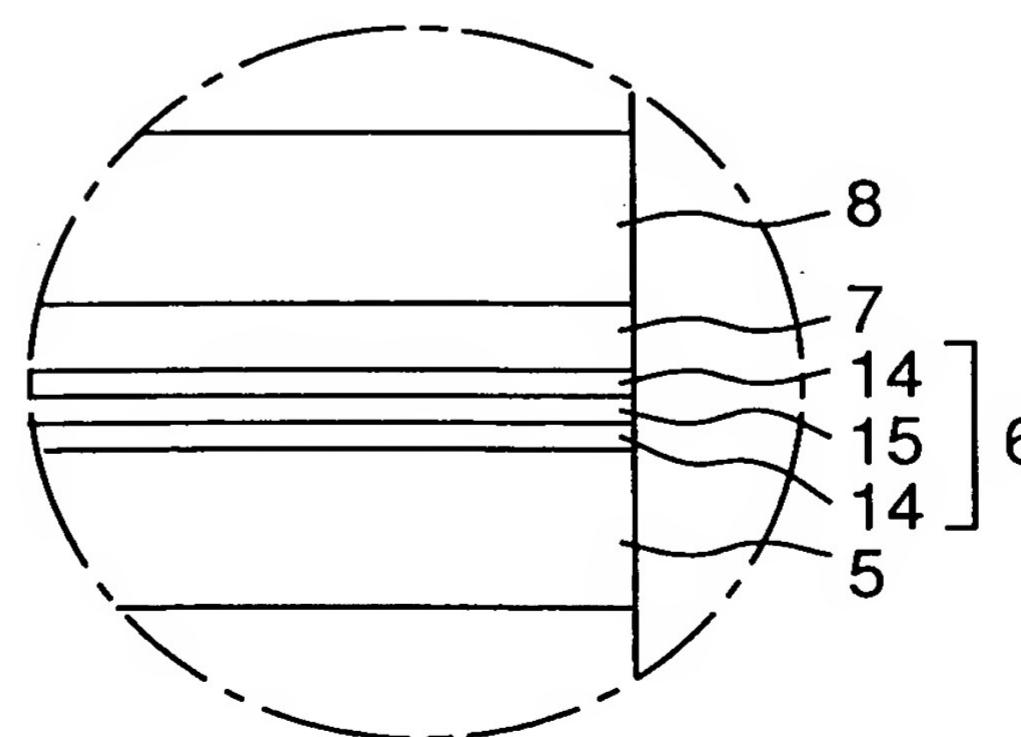


Fig. 2



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Fig.3

Frequency Capable of Modulating

Optical Output power

(Max. Frequency=●)

Threshold Current (○)

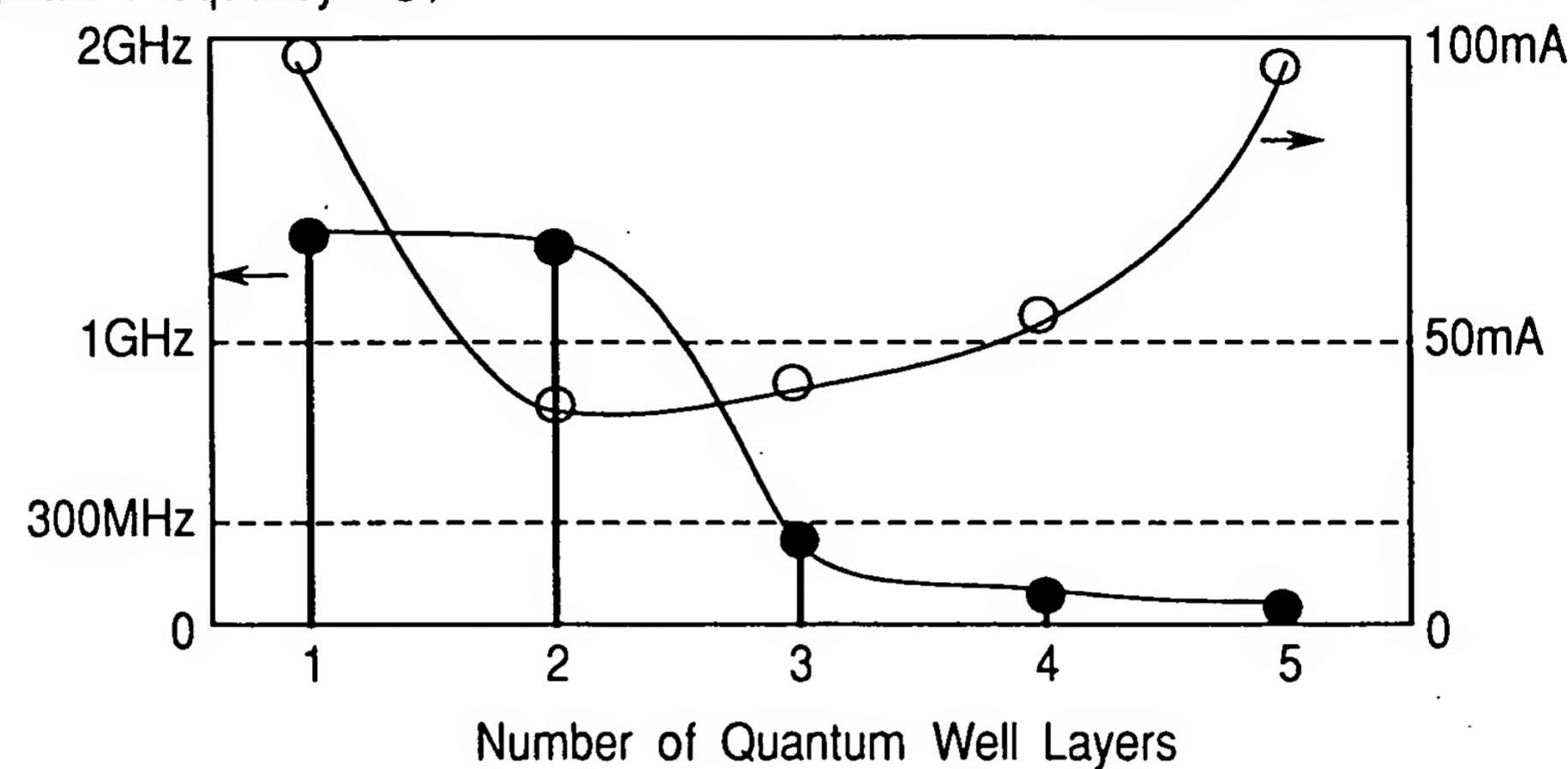


Fig.4

Frequency Capable of Modulating

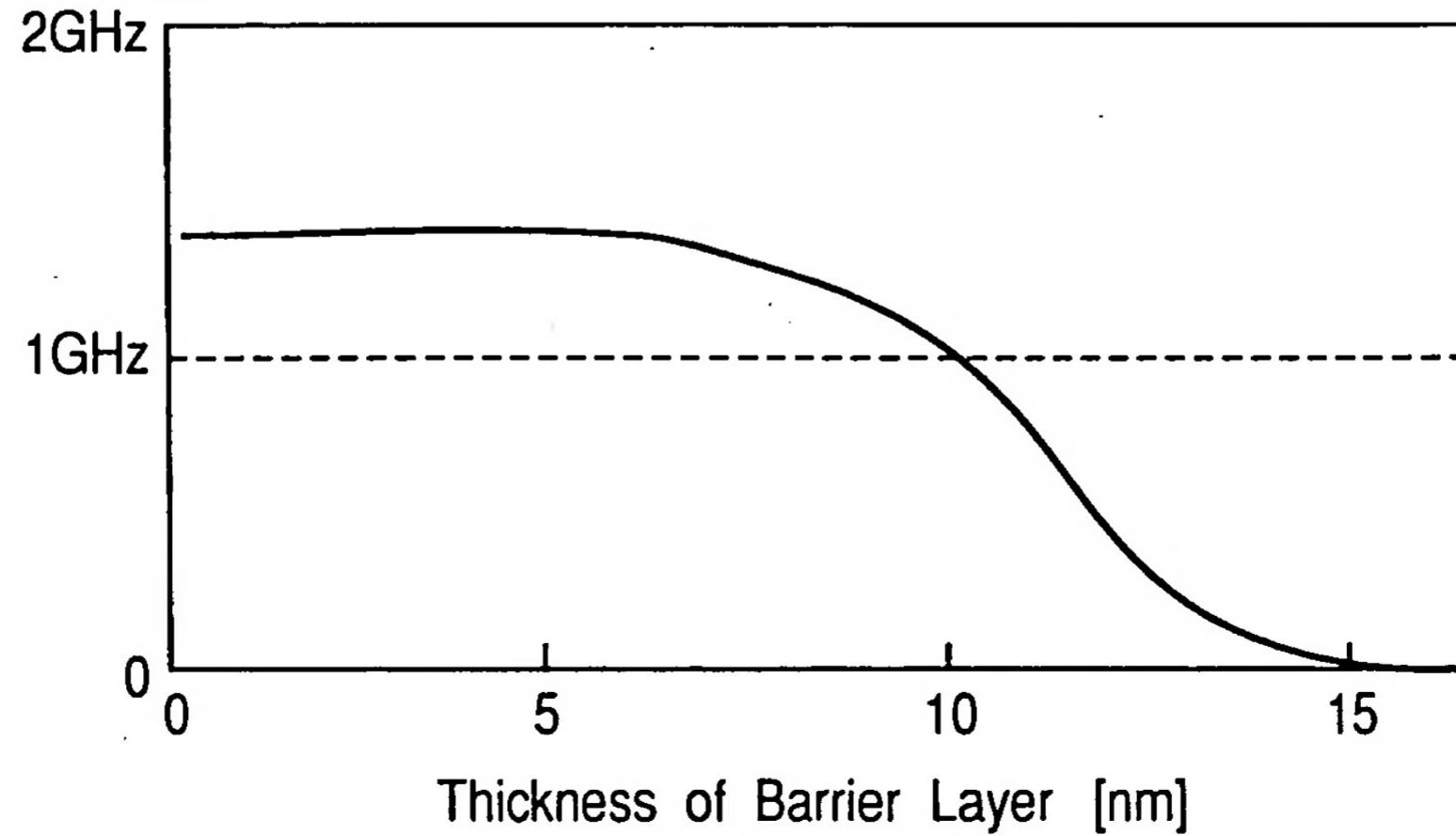
Optical Output power

2GHz

1GHz

0

Thickness of Barrier Layer [nm]



APPROVED
O.C. FIG.
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Fig.5

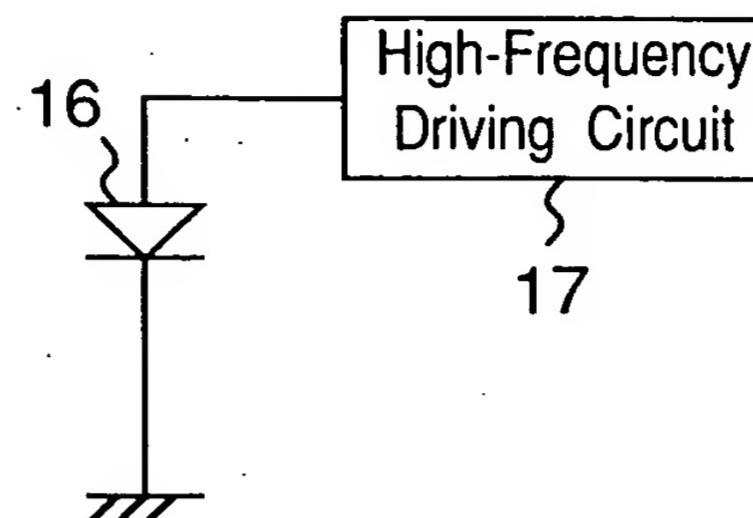


Fig.6

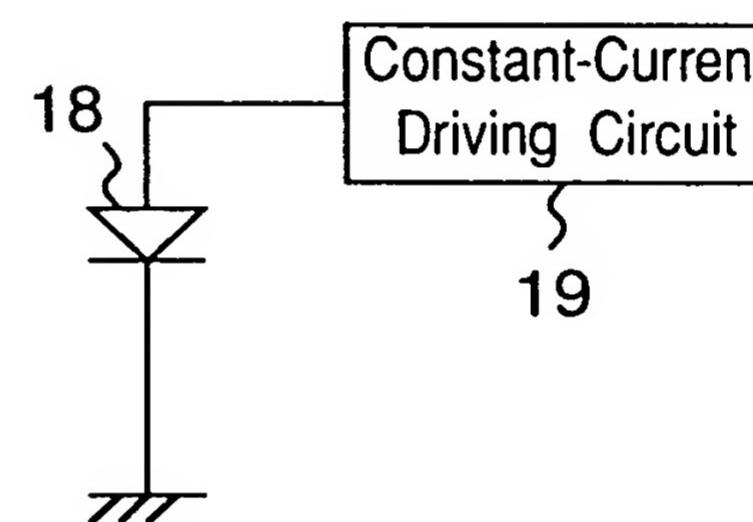
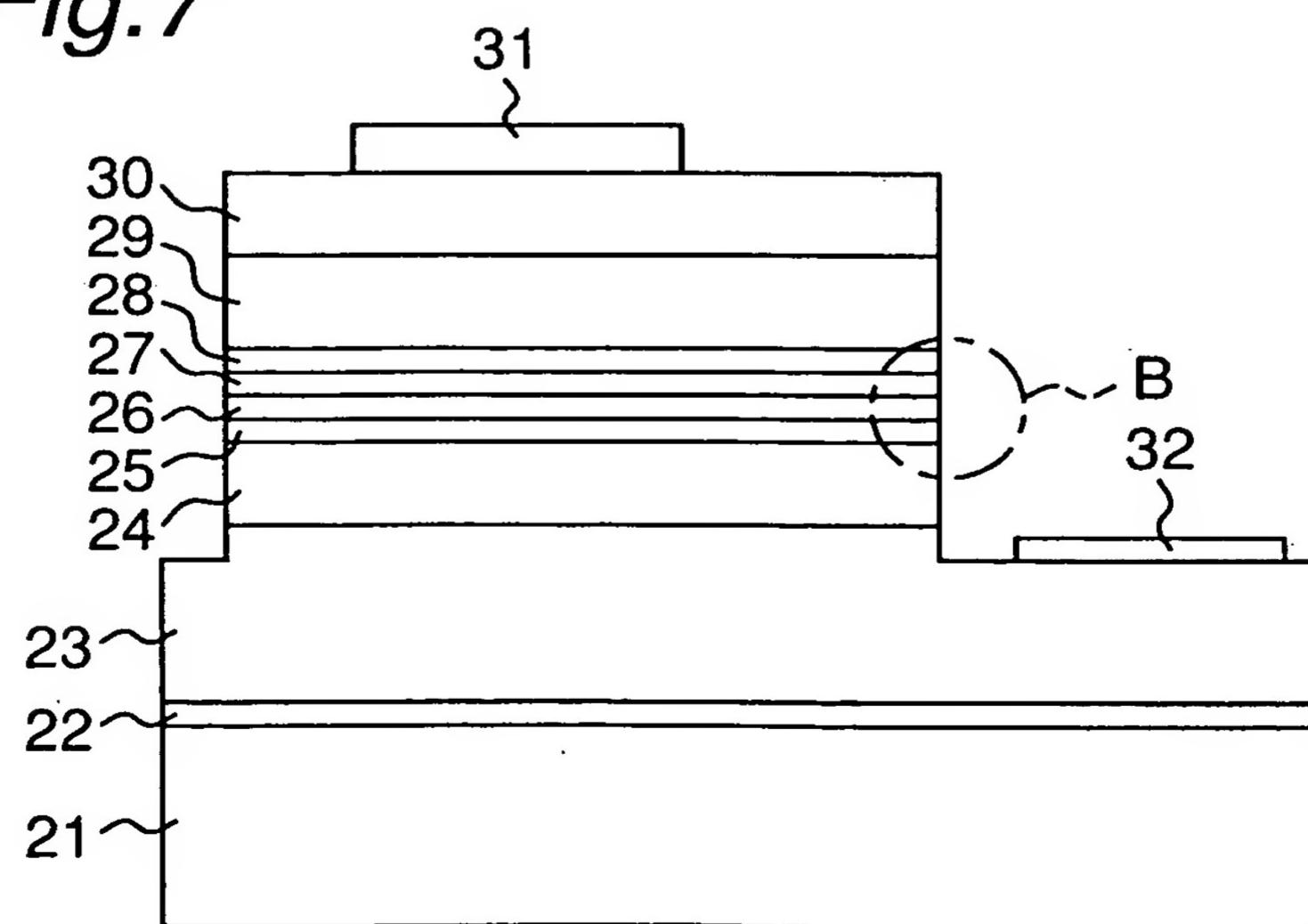


Fig.7



APPROVED D.G. FIG.
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Fig.8

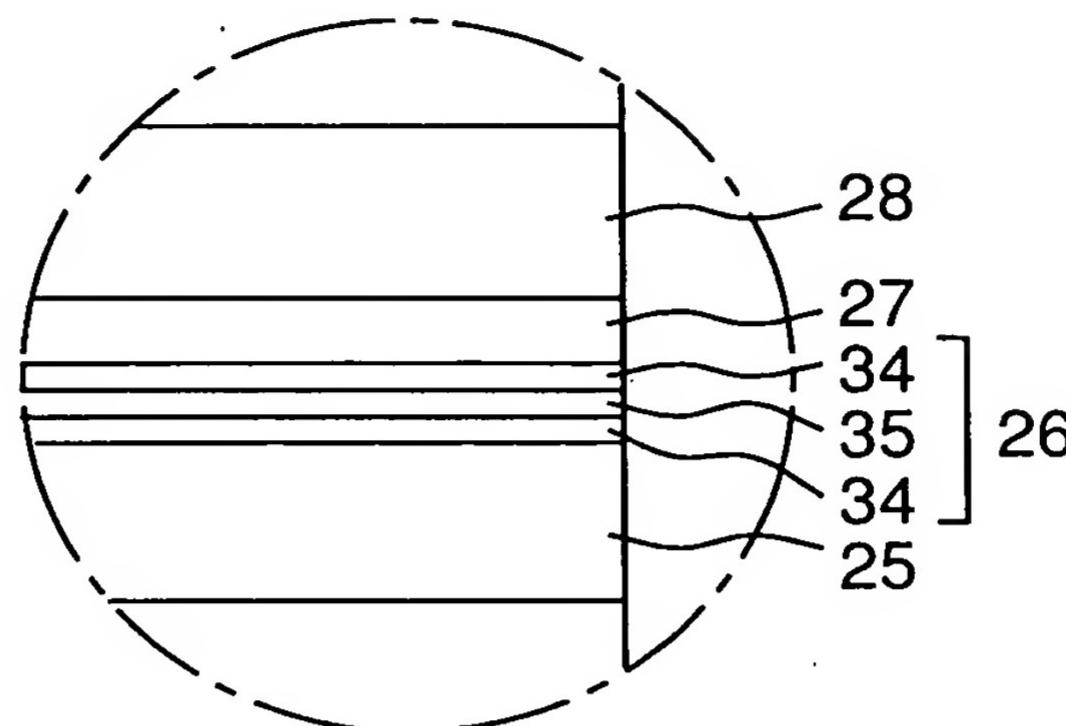
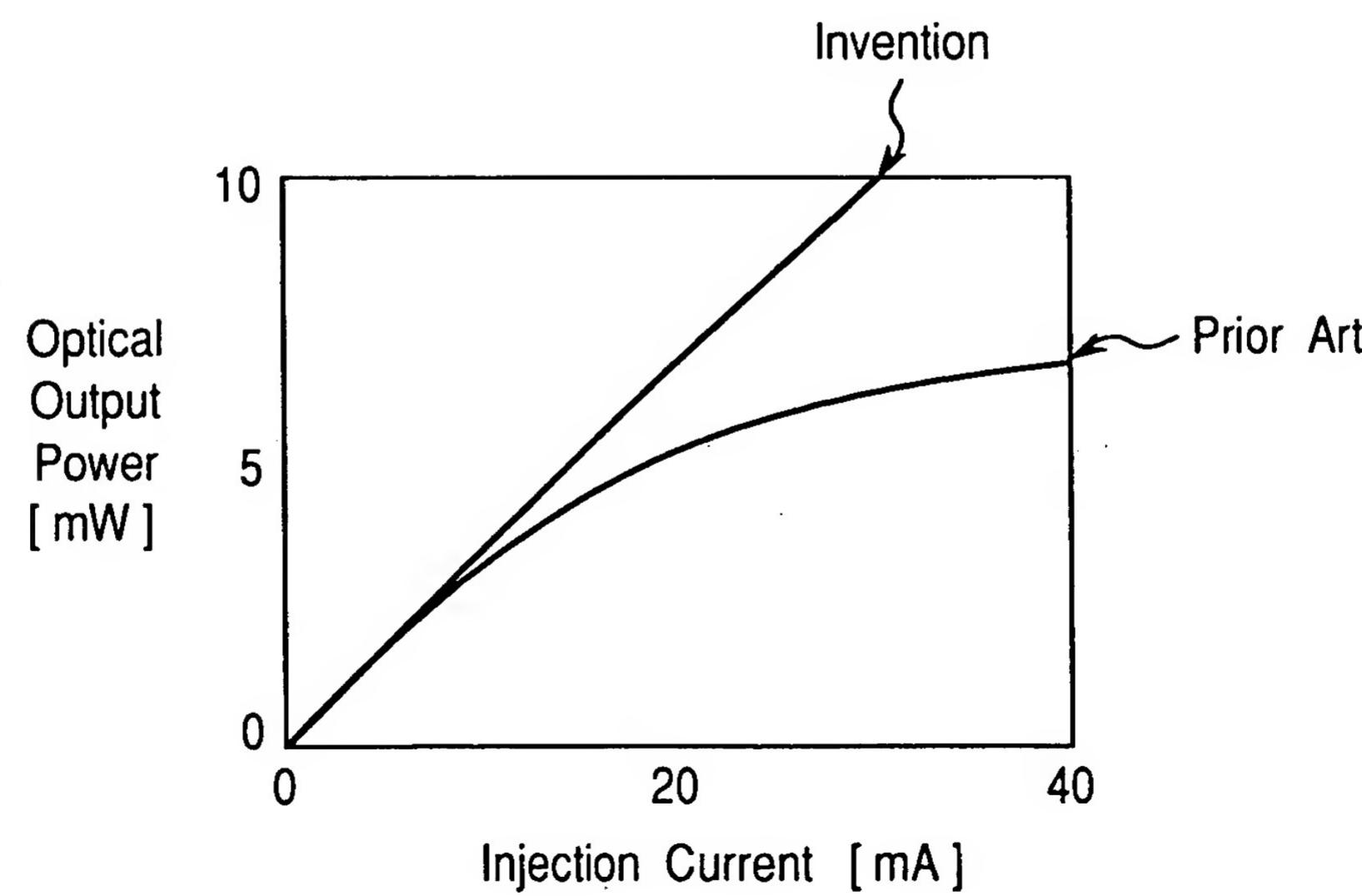


Fig.9



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Fig. 10

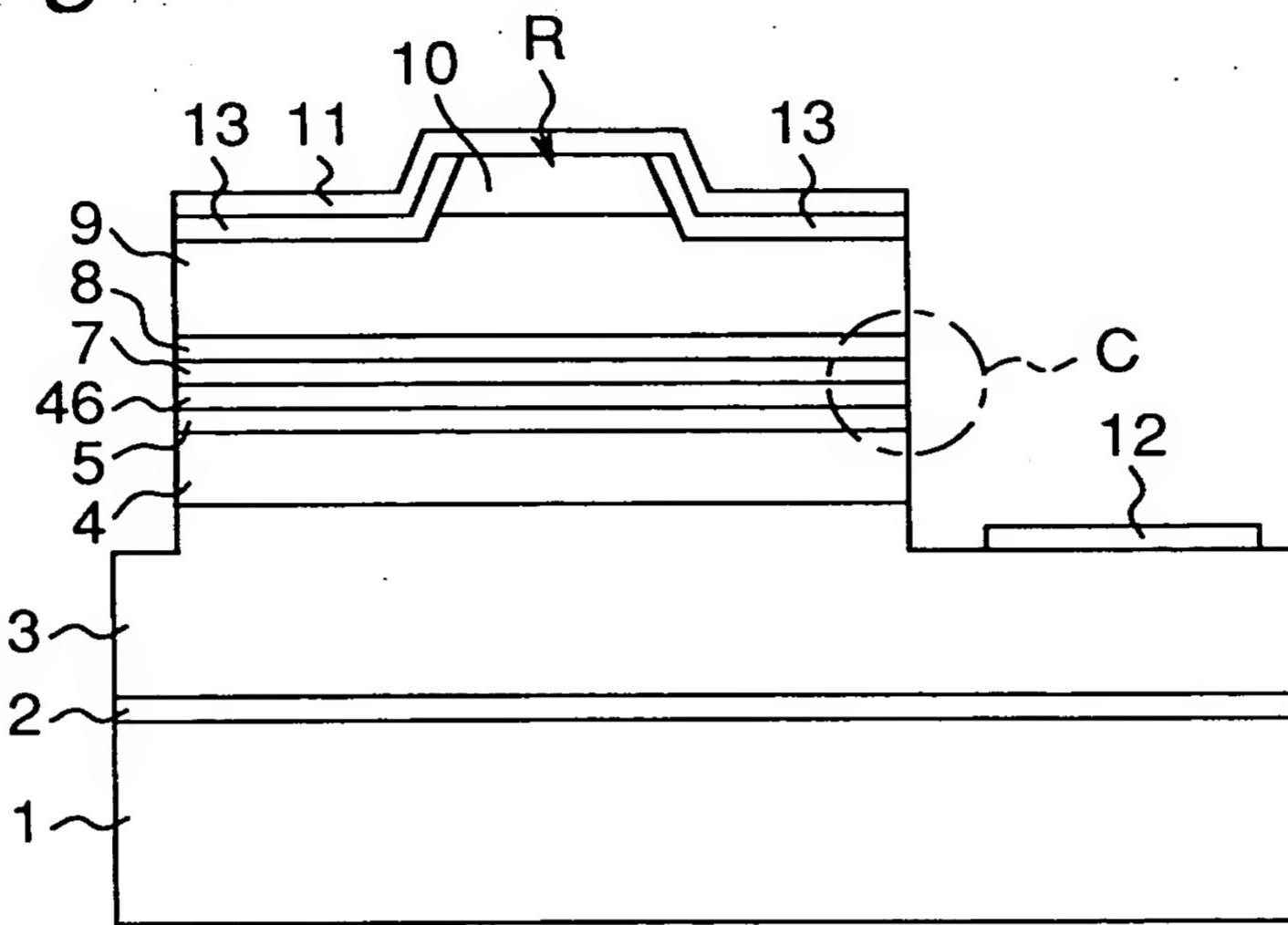
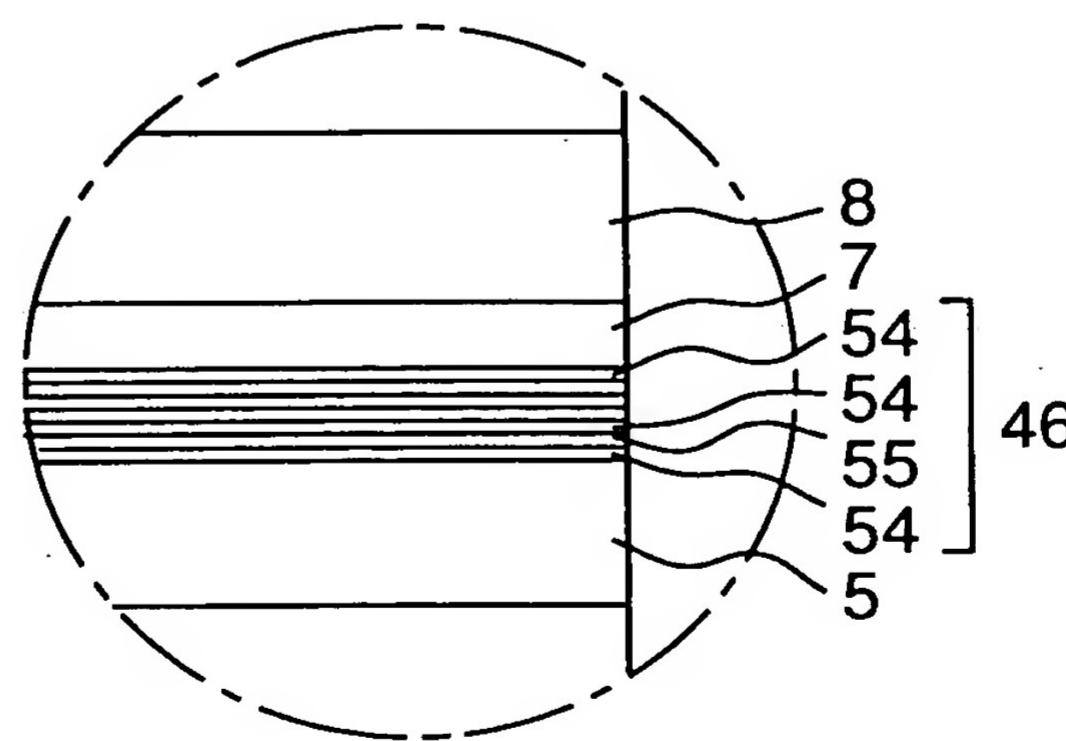


Fig. 11



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Fig. 12

Frequency Capable of Modulating
 Optical Output power
 (Max. Frequency = ●)

Threshold Current (○)

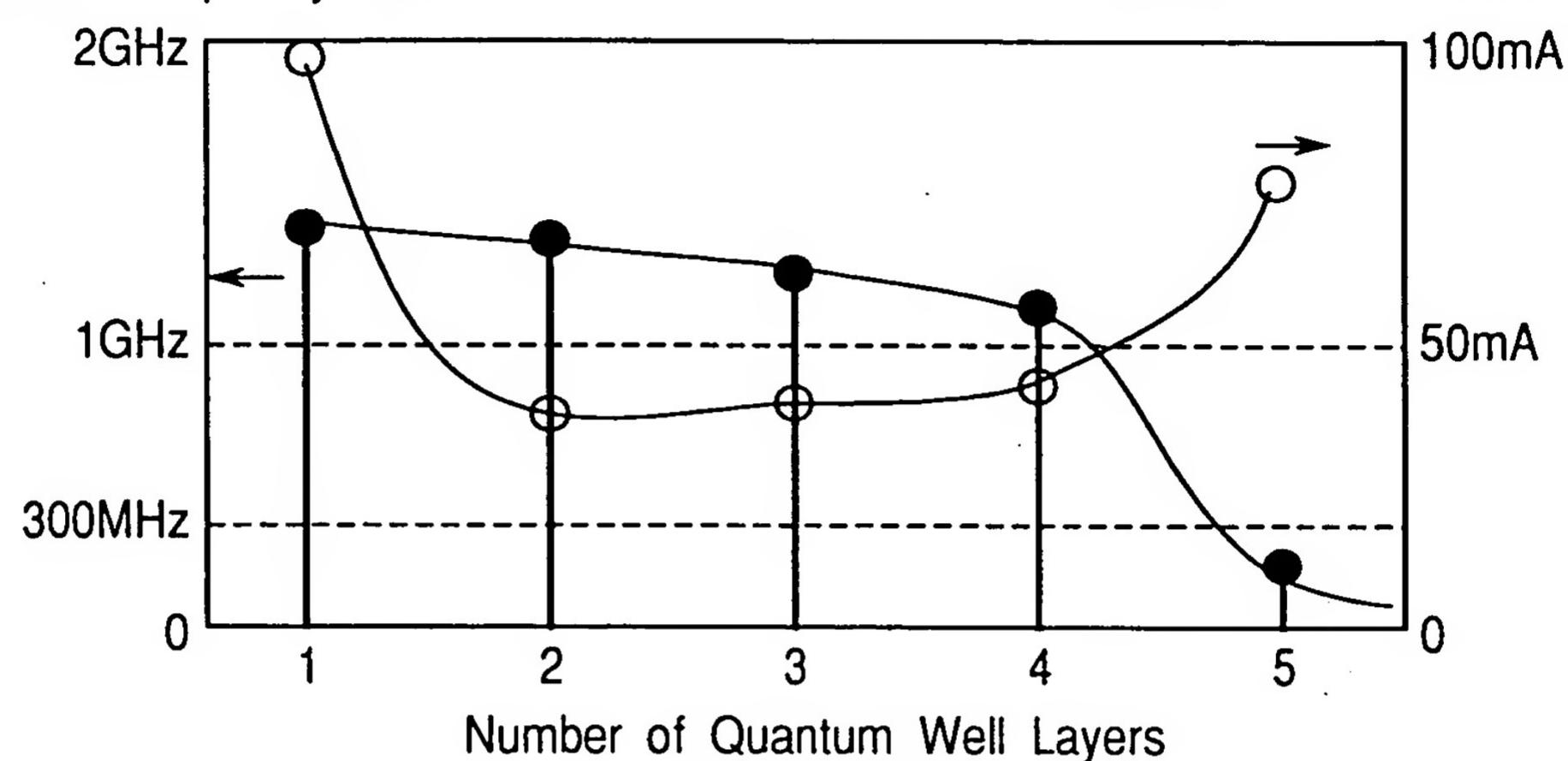
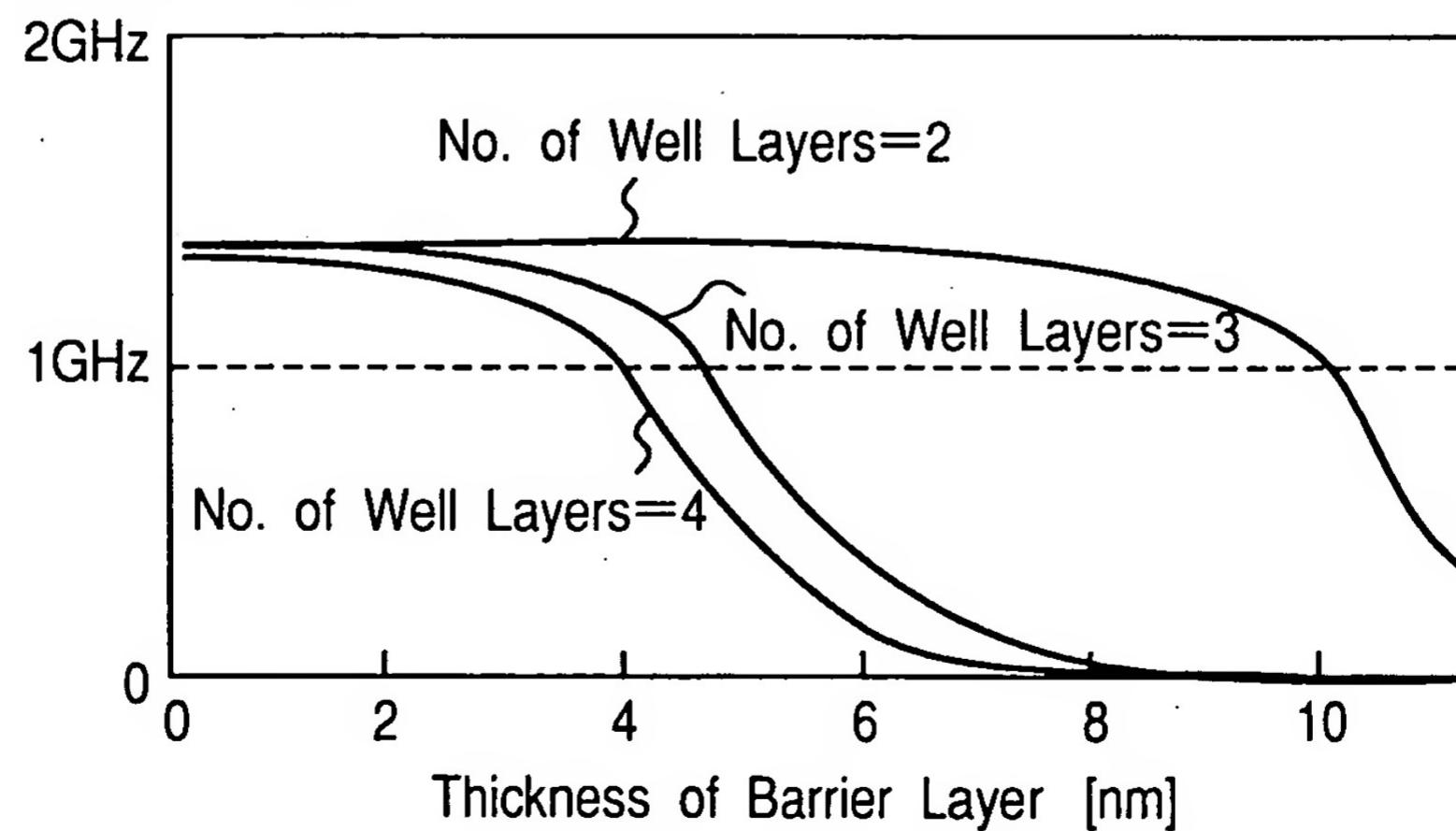


Fig. 13

Frequency Capable of Modulating
 Optical Output power



APPROVED TO G. FIG.
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Fig. 14

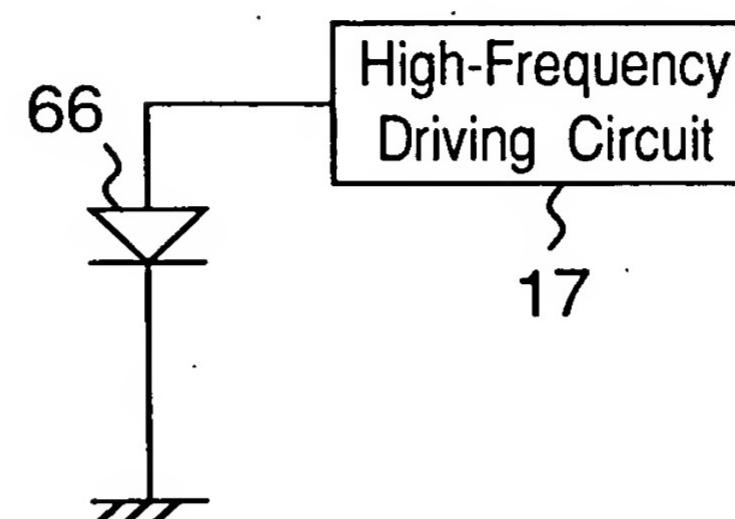


Fig. 15

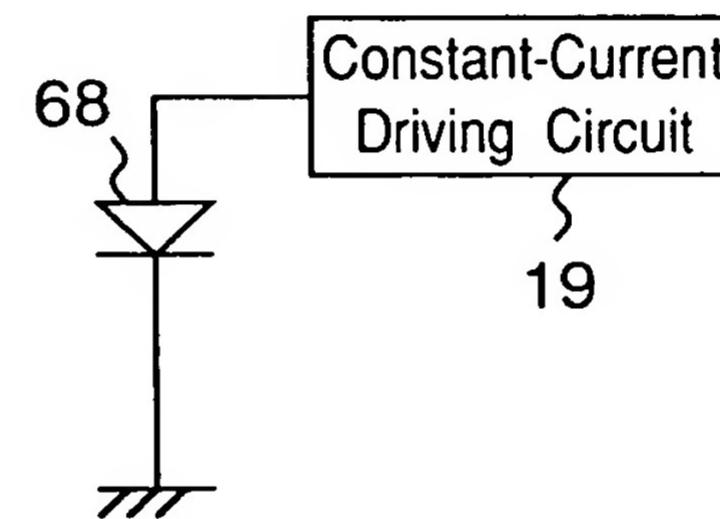
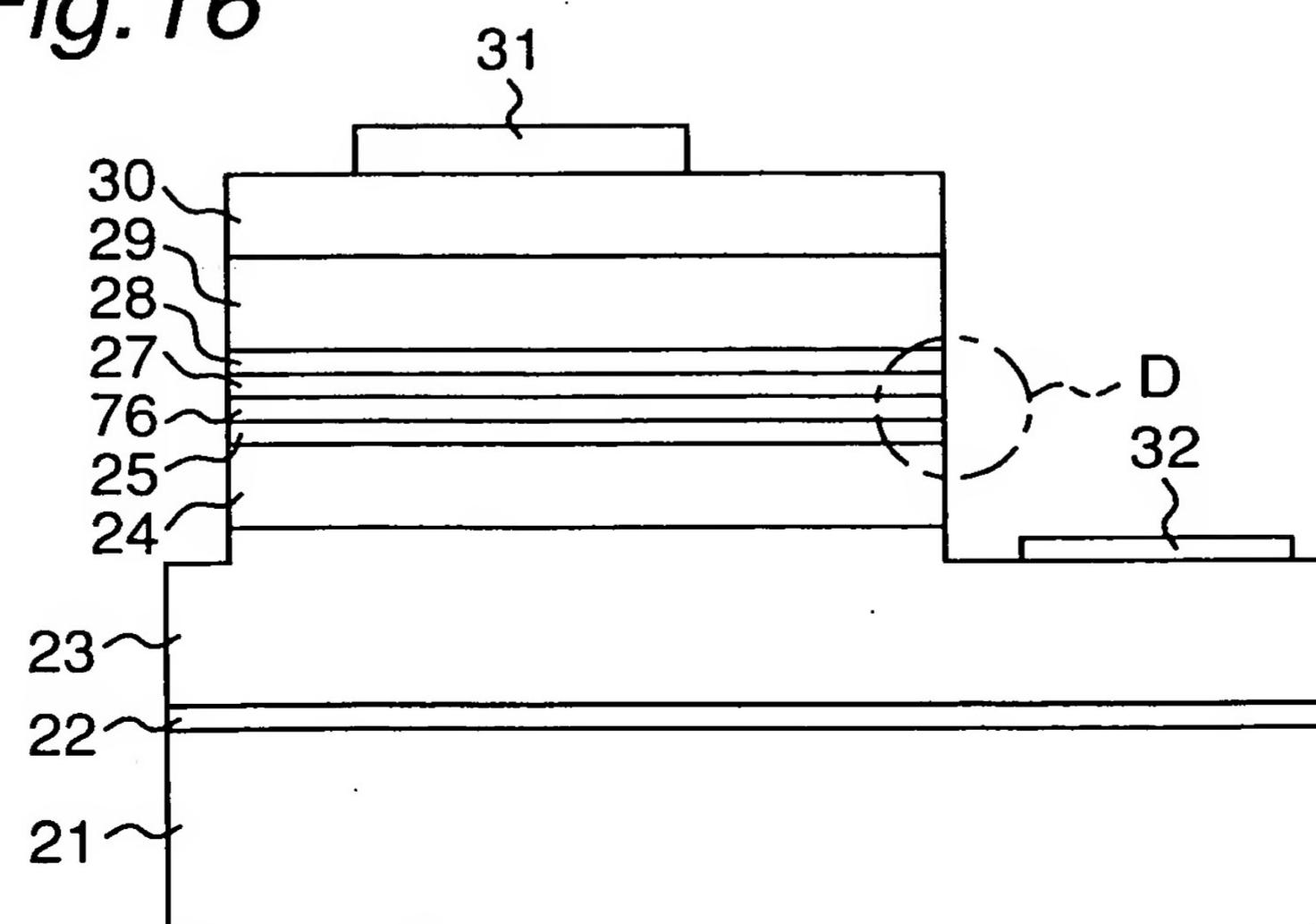


Fig. 16



APPROVED D.G. FIG.
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Fig.17

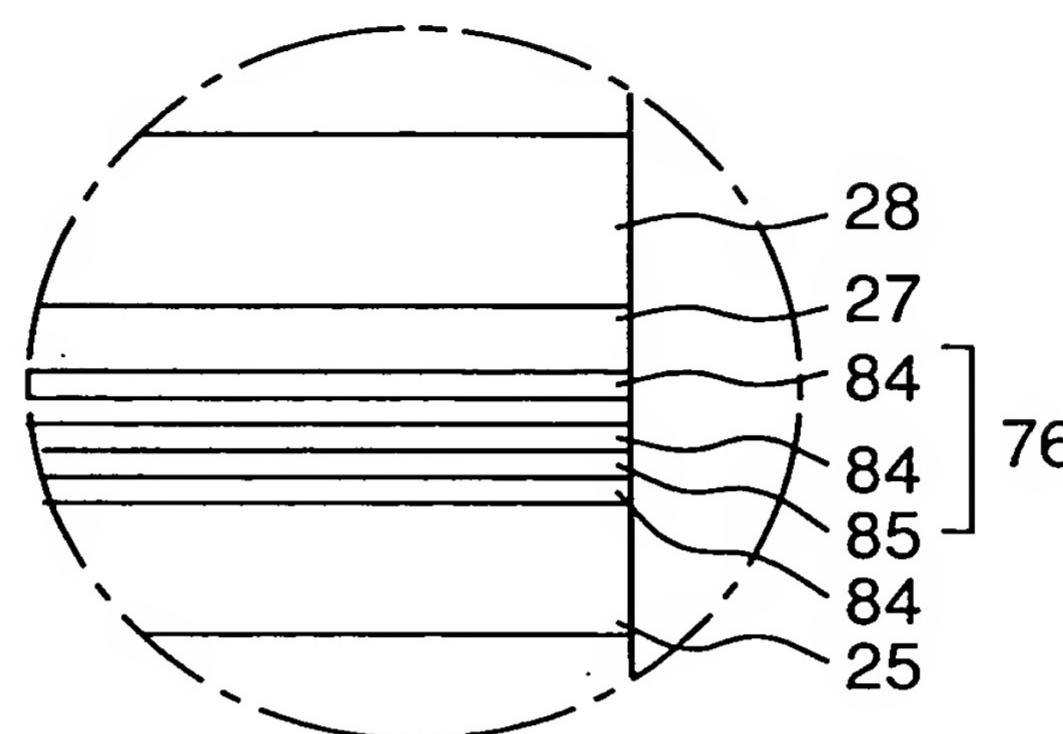
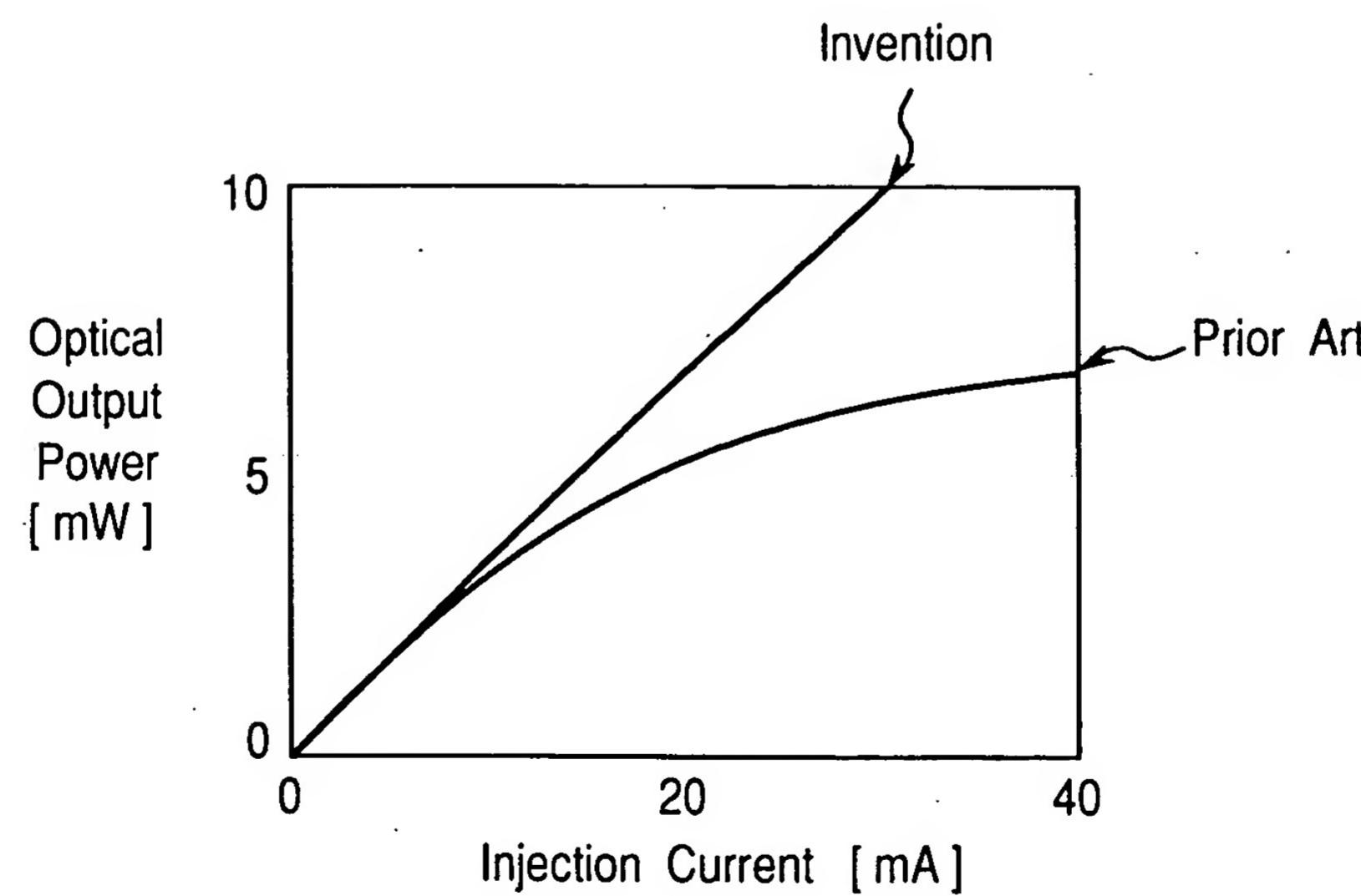
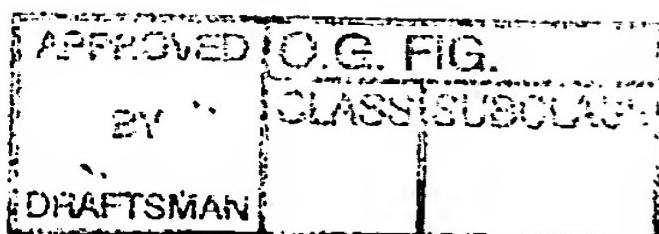


Fig.18





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Fig. 19

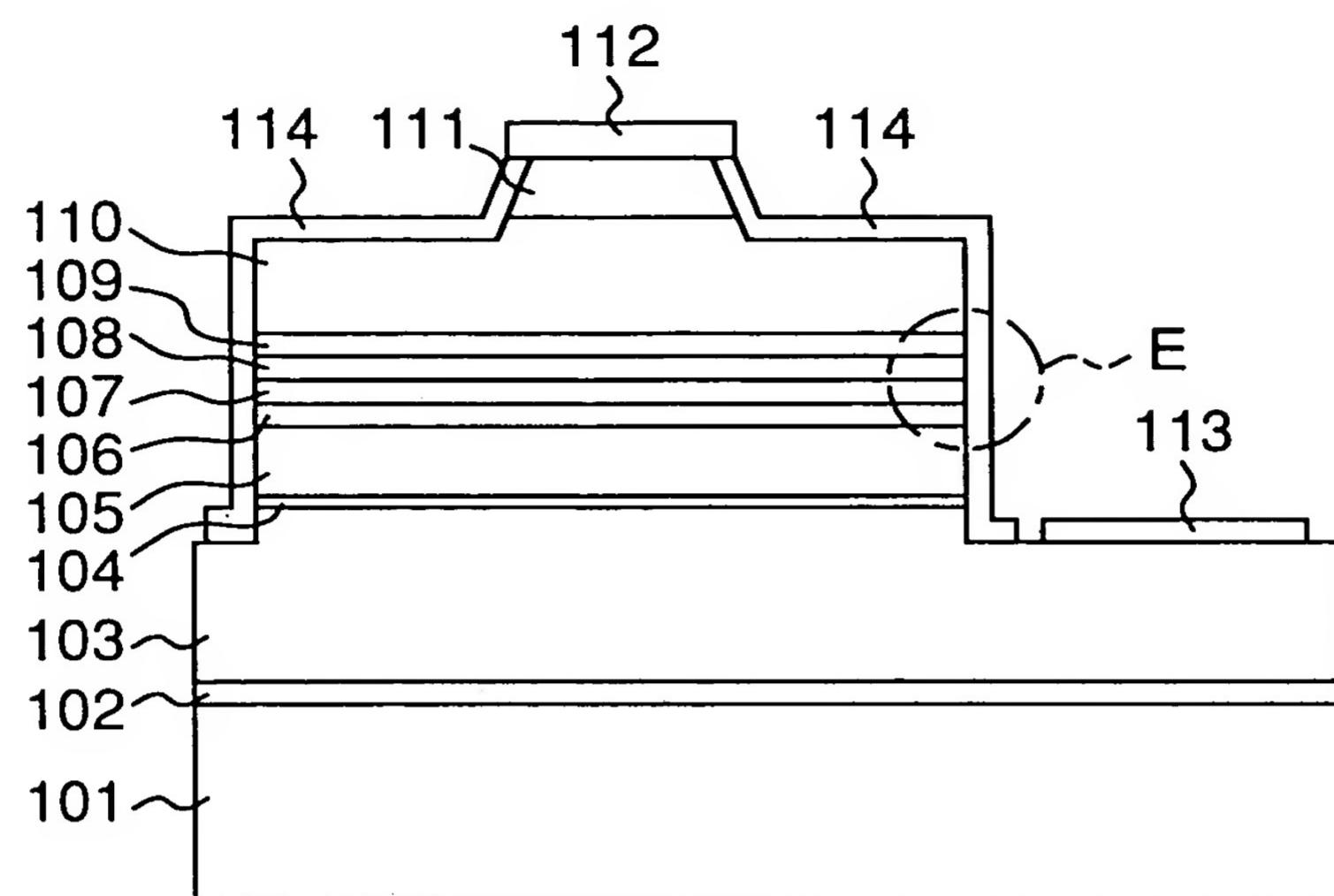
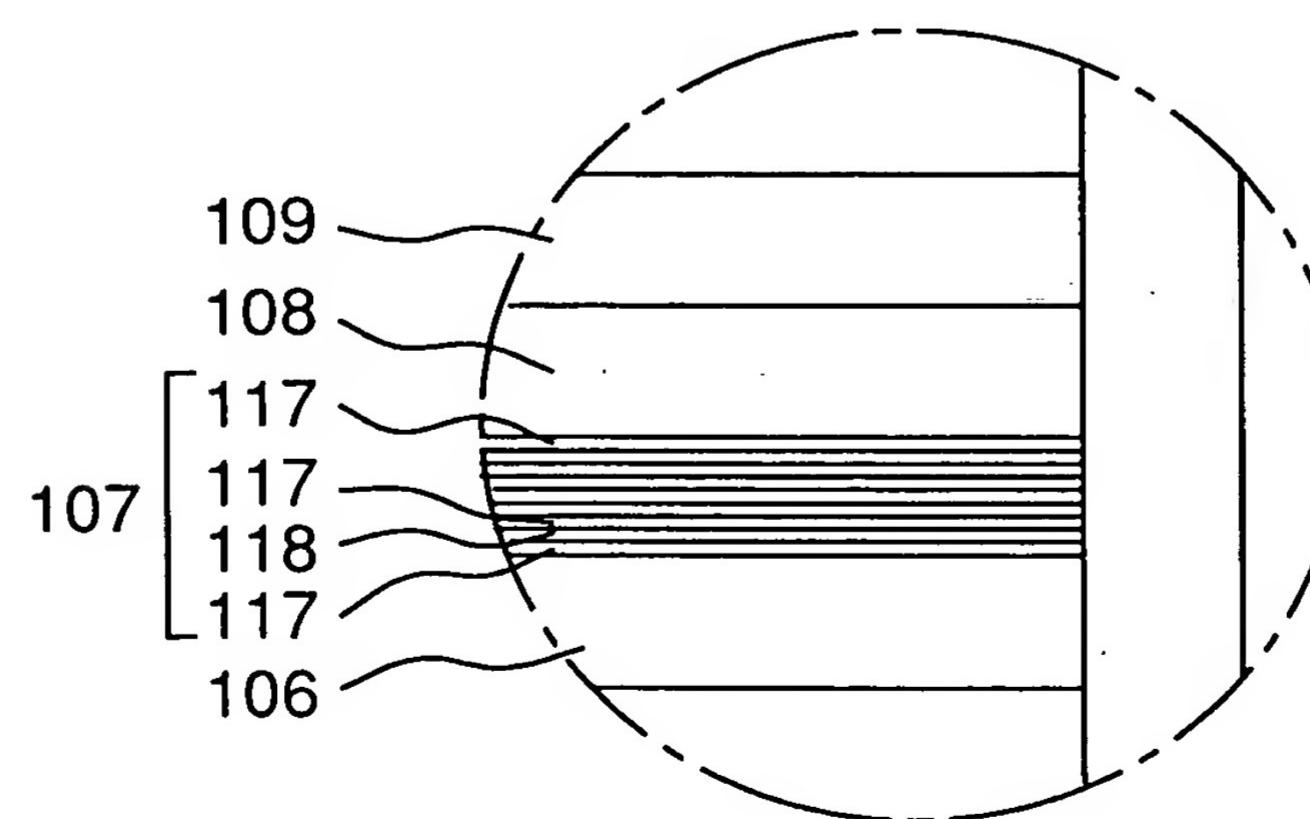


Fig. 20



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Fig.21

